

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|------|---|---|------------------|---------|------------------|
| L1 | 1 | "438"/\$.ccls. and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and (silicon adj carbide) and ("SiCOH") and ((oxygen or ("O.sub.2")) adj (implant\$6 or dop\$6)) and @ad<="20030214" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/03/31 14:19 |
| L2 | 1 | "257"/\$.ccls. and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and (silicon adj carbide) and ("SiCOH") and ((oxygen or ("O.sub.2")) adj (implant\$6 or dop\$6)) and @ad<="20030214" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/03/31 14:19 |
| L3 | 2 | semiconductor and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and (silicon adj carbide) and ("SiCOH") and ((oxygen or ("O.sub.2")) adj (implant\$6 or dop\$6)) and @ad<="20030214" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/03/31 14:19 |
| L4 | 89 | 438/629,637,639,640,667,668,672,675,700,701,713,978.ccls. and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and (silicon adj carbide) and @ad<="20030214" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/03/31 14:21 |
| L5 | 1 | 438/629,637,639,640,667,668,672,675,700,701,713,978.ccls. and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and (silicon adj carbide) and ((oxygen or ("O.sub.2")) adj (implant\$6 or dop\$6)) and @ad<="20030214" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/03/31 14:21 |
| S1 | 0 | (SiN same ((high adj density adj chemical adj vapor adj deposition) or ("HDCVD"))) and (("SiO.sub.2") same (dip adj etch)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/10/01 08:10 |

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|-----|----|---|---|----|----|------------------|
| S2 | 0 | (SiN with ((high adj density adj chemical adj vapor adj deposition) or ("HDCVD")))) and (("SiO.sub.2") with (dip adj etch)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/10/01 08:10 |
| S3 | 0 | (SiN and ((high adj density adj chemical adj vapor adj deposition) or ("HDCVD")))) and (("SiO.sub.2") and (dip adj etch)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/10/01 08:11 |
| S4 | 0 | ((Silicon adj nitride) or ("SiN")) and ((high adj density adj chemical adj vapor adj deposition) or ("HDCVD")) and (("SiO.sub.2") and (dip adj etch)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/10/01 08:13 |
| S5 | 70 | ((Silicon adj nitride) or ("SiN")) and ((high adj density adj chemical adj vapor adj deposition) or ("HDCVD")) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/10/01 08:21 |
| S6 | 79 | ((("SiO.sub.2") and (dip adj etch)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/10/01 08:21 |
| S7 | 16 | ((("SiO.sub.2") same (dip adj etch)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/10/01 08:21 |
| S8 | 8 | ((("SiO.sub.2") with (dip adj etch)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/10/01 08:21 |
| S11 | 79 | 438,629,637,639,640,667,668, 672,675,700,701,713,978.ccls. and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and (silicon adj carbide) and @ad<="20030214" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/03/31 14:20 |
| S12 | 38 | semiconductor and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and (silicon adj carbide) and @ad<="20030214" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/09/21 08:14 |

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|-----|----|--|---|----|----|------------------|
| S15 | 54 | semiconductor and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and (silicon adj carbide) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/09/27 13:08 |
| S16 | 10 | semiconductor and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and (silicon adj carbide) and ("SiCOH") | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/09/21 08:20 |
| S17 | 36 | semiconductor and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and (silicon adj carbide) and (dop\$6 or implant\$6) and (oxygen or ("O.sub.2")) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/09/21 08:22 |
| S18 | 12 | semiconductor and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and (silicon adj carbide) and ((dop\$6 or implant\$6) same (oxygen or ("O.sub.2"))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/09/21 08:35 |
| S19 | 5 | semiconductor and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and (silicon adj carbide) and ((dop\$6 or implant\$6) with (oxygen or ("O.sub.2"))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/09/21 08:35 |
| S20 | 12 | semiconductor and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and (((oxygen or ("O.sub.2")) same (silicon adj carbide)) or ("SiCOH")) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/09/27 13:21 |

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|-----|----|---|---|----|----|------------------|
| S21 | 10 | semiconductor and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and (((oxygen or ("O.sub.2")) same (dop\$6 or implant\$6) same ((silicon adj carbide) or ("SiC")) or ("SiCOH")) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/09/27 13:25 |
| S22 | 2 | 438/629,637,639,640,667,668, 672,675,700,701,713,978.ccls. and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and (((oxygen or ("O.sub.2")) same (dop\$6 or implant\$6) same ((silicon adj carbide) or ("SiC")) or ("SiCOH")) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/09/27 13:33 |
| S23 | 36 | "438"/\$.ccls. and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and ((dop\$6 or implant\$6) same (silicon adj carbide) or ("SiC")) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/09/27 13:36 |
| S24 | 35 | "257"/\$.ccls. and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and ((dop\$6 or implant\$6) same (silicon adj carbide) or ("SiC")) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/09/28 09:27 |
| S25 | 50 | semiconductor and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and ((dop\$6 or implant\$6) same (silicon adj carbide) or ("SiC")) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/09/27 13:36 |
| S26 | 8 | 438/629,637,639,640,667,668, 672,675,700,701,713,978.ccls. and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and ((dop\$6 or implant\$6) same (silicon adj carbide) or ("SiC")) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/09/28 09:24 |

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| S27 | 36 | "438"/\$.ccls. and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and ((dop\$6 or implant\$6) with (silicon adj carbide) or ("SiC")) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/09/27 13:41 |
| S28 | 35 | "257"/\$.ccls. and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and ((dop\$6 or implant\$6) with (silicon adj carbide) or ("SiC")) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/09/27 13:44 |
| S29 | 50 | semiconductor and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and ((dop\$6 or implant\$6) with (silicon adj carbide) or ("SiC")) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/09/28 07:15 |
| S30 | 5 | semiconductor and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and ((dop\$6 or implant\$6) near2 ((silicon adj carbide) or ("SiC"))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/09/28 07:30 |
| S31 | 10 | semiconductor and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and ((dop\$6 or implant\$6) with ((silicon adj carbide) or ("SiC"))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/09/28 07:26 |
| S32 | 3032 | semiconductor and ((dop\$6 or implant\$6) with ((silicon adj carbide) or ("SiC"))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/09/28 07:27 |
| S33 | 4829 | semiconductor and ((dop\$6 or implant\$6) same ((silicon adj carbide) or ("SiC"))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/09/28 07:28 |
| S34 | 794 | semiconductor and ((dop\$6 or implant\$6) near ((silicon adj carbide) or ("SiC"))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/09/28 07:29 |

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|-----|------|---|---|----|----|------------------|
| S35 | 2013 | semiconductor and ((doped) with ((silicon adj carbide) or ("SiC"))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/09/28 07:28 |
| S36 | 4050 | semiconductor and ((doped or implant\$6) same ((silicon adj carbide) or ("SiC"))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/09/28 07:29 |
| S37 | 676 | semiconductor and ((doped or implant\$6) near ((silicon adj carbide) or ("SiC"))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/09/28 07:29 |
| S38 | 3172 | semiconductor and ((doped) same ((silicon adj carbide) or ("SiC"))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/09/28 07:29 |
| S39 | 544 | semiconductor and ((doped) near ((silicon adj carbide) or ("SiC"))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/09/28 07:30 |
| S40 | 3172 | semiconductor and ((doped) same ((silicon adj carbide) or ("SiC"))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/09/28 07:30 |
| S41 | 0 | semiconductor with ((chemical adj mechanical adj polish\$6) or ("CMP")) with ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) with ((dop\$6 or implant\$6) near2 ((silicon adj carbide) or ("SiC"))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/09/28 07:31 |
| S42 | 0 | semiconductor near ((chemical adj mechanical adj polish\$6) or ("CMP")) near ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) near ((dop\$6 or implant\$6) near2 ((silicon adj carbide) or ("SiC"))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/09/28 07:32 |
| S43 | 0 | semiconductor near ((chemical adj mechanical adj polish\$6) or ("CMP")) near ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) near ((dop\$6 or implant\$6) near2 ((silicon adj carbide) or ("SiC"))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/09/28 07:32 |

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|-----|------|--|---|----|-----|------------------|
| S44 | 2 | semiconductor same ((chemical adj mechanical adj polish\$6) or ("CMP")) same ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) same ((dop\$6 or implant\$6) near2 ((silicon adj carbide) or ("SiC"))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/09/28 07:32 |
| S46 | 280 | 438/629,637,639,640,667,668,672,675,700,701,713,978.ccls. and ((dop\$6 or implant\$6) with (silicon adj carbide) or ("SiC")) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/09/28 09:24 |
| S47 | 8 | 438/629,637,639,640,667,668,672,675,700,701,713,978.ccls. and ((dop\$6 or implant\$6) same (oxygen or ("O.sub.2")) same ("SiCOH")) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/09/28 09:28 |
| S48 | 4 | "257"/\$.ccls. and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and ((dop\$6 or implant\$6) same (oxygen or ("O.sub.2")) same ("SiCOH")) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/09/28 10:26 |
| S49 | 300 | 438/629,637,639,640,667,668,672,675,700,701,713,978.ccls. and ((dop\$6 or implant\$6) same (silicon adj carbide) or ("SiC")) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/09/28 09:31 |
| S50 | 22 | "438"/\$.ccls. and ((dop\$6 or implant\$6) same (oxygen or ("O.sub.2")) same ("SiCOH")) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/09/28 10:26 |
| S51 | 18 | "257"/\$.ccls. and ((dop\$6 or implant\$6) same (oxygen or ("O.sub.2")) same ("SiCOH")) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/09/28 10:26 |
| S59 | 1875 | (257/774).CCLS. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/03/31 14:17 |

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|-----|-----|---|---|----|----|------------------|
| S68 | 612 | "438"/\$.ccls. and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and (silicon adj carbide) and @ad<="20030214" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/03/31 14:17 |
| S69 | 28 | "438"/\$.ccls. and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and (silicon adj carbide) and @ad<="20030214" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/05/20 14:06 |
| S70 | 7 | 438/629,637,639,640,667,668, 672,675,700,701,713,978.ccls. and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and (silicon adj carbide) and @ad<="20030214" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/05/25 12:25 |
| S71 | 28 | "438"/\$.ccls. and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and (silicon adj1 carbide) and @ad<="20030214" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/05/25 12:13 |
| S72 | 38 | semiconductor and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and (silicon adj1 carbide) and @ad<="20030214" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/05/25 12:20 |
| S73 | 7 | 438/629,637,639,640,667,668, 672,675,700,701,713,978.ccls. and ((chemical adj mechanical adj polish\$6) or ("CMP")) and ((high adj density adj plasma adj chemical adj vapor adj deposit\$4) or ("HDPCVD")) and (silicon adj carbide) and @ad<="20030214" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/05/25 12:25 |

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|-----|----|---|--------------------|----|-----|------------------|
| S76 | 29 | (("20040048468") or ("20020063334") or ("20020115285") or ("6261951") or ("6642145") or ("6432822") or ("6429128") or ("6140226") or ("6593660") or ("6649531") or ("6656840") or ("6737747") or ("6566242") or ("6362085") or ("6656644") or ("6620633") or ("6380555") or ("4532150") or ("4854263") or ("5238866") or ("5465680") or ("5773100") or ("5989623") or ("6040022") or ("6100559") or ("6174810") or ("6365518") or ("4029522") or ("5877513")).PN. | US-PGPUB; USPAT | OR | OFF | 2005/01/28 10:44 |
| S77 | 1 | ("20040097072").PN. | US-PGPUB; USPAT | OR | OFF | 2005/01/28 10:44 |